

# B Santic

## List of Publications by Year in descending order

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28  
papers

1,158  
citations

687363

13  
h-index

526287

27  
g-index

28  
all docs

28  
docs citations

28  
times ranked

1001  
citing authors

#	ARTICLE	IF	CITATIONS
1	Measurement of the refractive index and thickness of a transparent film from the shift of the interference pattern due to the sample rotation. <i>Thin Solid Films</i> , 2010, 518, 3619-3624.	1.8	13
2	On the evaluation of optical parameters of a thin semiconductor film from transmission spectra, and application to GaN films. <i>Measurement Science and Technology</i> , 2008, 19, 105303.	2.6	8
3	Statistics of the Mg acceptor in GaN in the band model. <i>Semiconductor Science and Technology</i> , 2006, 21, 1484-1487.	2.0	5
4	On the determination of the statistical characteristics of the magnesium acceptor in GaN. <i>Superlattices and Microstructures</i> , 2004, 36, 445-453.	3.1	6
5	The impact of deep levels on the photocurrent transients in semi-insulating GaAs. <i>Journal of Electronic Materials</i> , 2003, 32, 1100-1106.	2.2	4
6	On the hole effective mass and the free hole statistics in wurtzite GaN. <i>Semiconductor Science and Technology</i> , 2003, 18, 219-224.	2.0	52
7	Electrical conductivity in mixed-alkali iron phosphate glasses. <i>Journal of Non-Crystalline Solids</i> , 2001, 283, 119-128.	3.1	58
8	The dc electrical conductivity of iron phosphate glasses. <i>Journal of Non-Crystalline Solids</i> , 2001, 296, 65-73.	3.1	55
9	Electrical relaxation in mixed alkali iron pyrophosphate glasses. <i>Journal of Non-Crystalline Solids</i> , 2000, 263-264, 299-304.	3.1	38
10	Origin of defect-related photoluminescence bands in doped and nominally undoped GaN. <i>Physical Review B</i> , 1999, 59, 5561-5567.	3.2	260
11	Nature of the 2.8 eV photoluminescence band in Mg doped GaN. <i>Applied Physics Letters</i> , 1998, 72, 1326-1328.	3.3	342
12	Ionized donor bound excitons in GaN. <i>Applied Physics Letters</i> , 1997, 71, 1837-1839.	3.3	66
13	Analysis of transient phenomena in GaAs within the metastable model. <i>Physica Status Solidi (B): Basic Research</i> , 1996, 195, 465-474.	1.5	0
14	Optical cross section for the $EL2 \rightarrow EL2^*$ metastable transformation. <i>Physical Review B</i> , 1995, 51, 11117-11119.	3.2	5
15	A comparative study of deep levels in undoped semi-insulating gallium arsenide wafers using thermally stimulated current spectra. <i>Journal Physics D: Applied Physics</i> , 1995, 28, 934-938.	2.8	10
16	Trapping and recombination processes via deep level T3 in semi-insulating gallium arsenide. <i>Journal of Electronic Materials</i> , 1993, 22, 403-407.	2.2	6
17	Photoconductivity transients and photosensitization phenomena in semi-insulating GaAs. <i>Journal of Applied Physics</i> , 1993, 73, 5181-5184.	2.5	7
18	Electrical Properties of $Cu_xGa_{1-x}In_{1-x}Te_2$ Semiconductors. <i>Physica Status Solidi A</i> , 1992, 133, 137-146.	1.7	10

#	ARTICLE	IF	CITATIONS
19	Calculation of the glow curve shape " application to the thermally stimulated currents (TSC). Solid State Communications, 1991, 79, 535-538.	1.9	6
20	The analysis of low-temperature photoconductivity evolution in semi-insulating GaAs. Journal of Physics Condensed Matter, 1991, 3, 5817-5824.	1.8	6
21	EL2 related deep traps in semi-insulating GaAs. Applied Physics Letters, 1991, 58, 278-280.	3.3	34
22	Light-intensity dependence of slow-relaxation phenomena in semi-insulating GaAs. Applied Physics A: Solids and Surfaces, 1990, 51, 379-381.	1.4	13
23	Quenching and enhancement of photoconductivity in semi-insulating GaAs. Solid State Communications, 1990, 74, 847-850.	1.9	14
24	Thermoelectric effect spectroscopy of deep levels" application to semi-insulating GaAs. Applied Physics Letters, 1990, 56, 2636-2638.	3.3	55
25	Trap-induced photoconductivity in semi-insulating GaAs. Journal of Applied Physics, 1990, 67, 1408-1411.	2.5	26
26	Optically enhanced photoconductivity in semi-insulating gallium arsenide. Applied Physics Letters, 1989, 54, 810-812.	3.3	34
27	A simple method for determination of the Hall constant. Journal of Physics E: Scientific Instruments, 1989, 22, 997-1000.	0.7	4
28	Crystal data for CuGaIn <sub>1-x</sub> Te <sub>2</sub> . Journal of Applied Crystallography, 1983, 16, 576-576.	4.5	21